Hall Effect on CoZrGd films

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The Hall effect in amorphous films which has soft magnetic properties were studied in several works[1-4]. It was found that the spontaneous Hall coefficient of amorphous RE-TM films(RE: Rare Earth metal, TM: 3d transition metal) is anormally larger than that of the other soft magnetic materials. The other particularity of amorphous RE-TM films which has ferrimagnetic structure, is that the sign of Hall voltage(V_{Hall}) is changed to oposite near the compansation temperature($T_{comp.}$).

The Hall properties of amorphous CoZrGd films(15 at.% < Gd < 28 at.%) was compared with its magnetic properties, since the temperature dependancy of saturation magnetization is easily controlled by changing Co and Gd composition ratio. By considering the sub-lattice magnetization M_{Gd} and M_{Co} , the calculated spontaneous Hall resistivity increases slightly from $1.8 \times 10^{-12}~W\text{-m/G}$ to $3 \times 10^{-12}~W\text{-m/G}$ as Gd concentration increased. It is revealed that almost all of electron scattering is originated from skew scattering. An anomalous over-fluctuation of ρ_{H} most marked around T_{comp} is also reported.

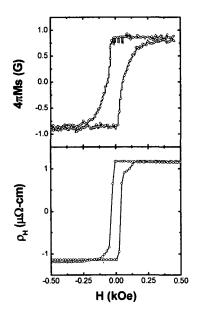


Fig. 1. Magnetic and Hall hysterisis loop of Gd 22 at.% film at room temperature.

References

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